

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (low adj pressure or vacuum) and (temperature or celsius or kelvin or fahrenheit)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:43
L2	2	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (low adj pressure or vacuum) and (temperature or celsius or kelvin or fahrenheit) and bonding).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:43
L3	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) adj (low adj pressure or vacuum) and bonding).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:44
L4	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) with (low adj pressure or vacuum) and bonding).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:44

L5	13	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) with (temperature or celsius or fahrenheit or kelvin) and bonding). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:44
L6	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) with vacuum and (substrate or wafer) and (first and second) with (temperature or celsius or fahrenheit or kelvin) and bonding). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:48
L7	16	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) with vacuum and (substrate or wafer) and (first and second) with (temperature or celsius or fahrenheit or kelvin) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:48
L8	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) adj (low adj pressure or vacuum) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:54

L9	68	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) with (low adj pressure or vacuum) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:55
L10	1673	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:56
L11	1213	438/458.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:56
L12	11	(10 or 11) and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 06:56
L13	783	257/e21.567.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:00
L14	1137	257/e21.568.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:01
L17	13	9 and (13 14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:15
L18	325	257/e21.561.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:16
L19	615	257/e21.545.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:16

L20	9665	((first and second) with (low adj pressure or vacuum) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:22
L21	127454	((first and second) and (low adj pressure or vacuum) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:22
L22	681	((first and second) adj (low adj pressure or vacuum) and bonding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:22
L23	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) adj (low adj pressure or vacuum) and (bonding or joining)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:23
L24	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) near4 (low adj pressure or vacuum) and (bonding or joining)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:23
L25	0	((implant\$4 or implantation or doping) with ("h. sub.2" or hydrogen) and (drying or cleaning) and (substrate or wafer) and (first and second) with (low adj pressure or vacuum) and (bonding or joining)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:23

L26	136	438/480.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:26
L27	804	438/526.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:30
L28	1048	438/530.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:31
L29	713	(anneal\$4 or heat adj treat\$4) and 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:31
L30	23963	(anneal\$4 or heat adj treat\$4) with (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:32
L31	42	(27 28) and 30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:32
L32	66	(10 11) and 30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:34
L33	208022	(clean\$4 or dry\$4) with (vacuum or low adj pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:36
L34	9	32 and 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:37
L35	0	(10/334176).APP.	USPAT; USOCR	OR	ON	2008/04/07 07:50

L40	1	"20040126993" and (low adj pressure or vacuum)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 07:57
L41	1	11 and 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:07
L42	4	10 and 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:08
L43	4279	(bonding or joining) with (substrate or wafer) with (vacuum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:11
L44	133	(10 11) and 43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:11
L45	353	(bonding or joining) with (substrate or wafer) with (vacuum) with temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:45
L46	22	(bonding or joining) with two adj (substrate or wafer) with (vacuum) with temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:46
L47	64	(bonding or joining) with two adj (substrate or wafer) with (vacuum) same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:48
L48	23	(bonding or joining) with two adj (substrate or wafer) with (low adj pressure or vacuum) with temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:53

L49	66	(bonding or joining) with two adj (substrate or wafer) with (low adj pressure or vacuum) same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 08:53
L50	0	"20040126993" and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 09:38
L51	1	"20040126993" and quartz	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 09:39
L52	0	"20050081958" and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 09:39
L53	2	"6,846,718".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 09:47

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